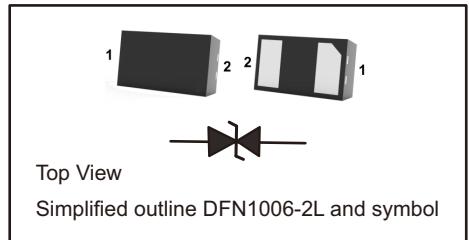




## Transient Voltage Suppressors for ESD Protection

### FEATURES

- Stand-off voltage:  $\pm 7\text{V}$  Max
- Transient protection for each line according to
  - IEC61000-4-2(ESD):  $\pm 30\text{kV}$  (contact)
  - IEC61000-4-4 (EFT): 40A (5/50ns)
  - IEC61000-4-5(surge): 6A (8/20 $\mu\text{s}$ )
- Ultra-low capacitance:  $C_J = 10\text{pF}$  typ
- Low leakage current:
- Low clamping voltage:  $V_{CL} = 12.0\text{V}$  typ. @  $I_{PP} = 16\text{A}$  (TLP)
- Solid-state silicon technology
- HF Product

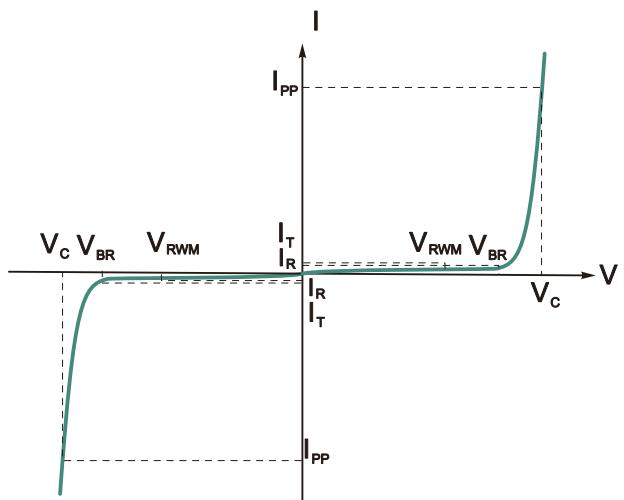


### Applications

- Cellular handsets
- USB VBUS and CC Line Protection
- Microphone Line Protection
- GPIO Protection

### Electronics Parameter

Parameter	Symbol
Maximum Reverse Peak Pulse Current	$I_{PP}$
Clamping Voltage @ $I_{PP}$	$V_C$
Peak Reverse Working Voltage	$V_{RWM}$
Reverse Leakage Current @ $V_{RWM}$	$I_R$
Breakdown Voltage @ $I_T$	$V_{BR}$
Test Current	$I_T$





Absolute Maximum Ratings And Characteristics ( Ta = 25 °C )

Parameter	Symbol	Value	Unit
Peak Pulse Power (8/20 μS)	P <sub>pk</sub>	78	W
Peak Pulse Current	I <sub>pp</sub>	6.0	A
ESD per IEC 61000-4-2 (Air) ESD per IEC 61000-4-2 (Contact)	V <sub>ESD</sub>	±30 ±30	kV
Operating Temperature Range	T <sub>J</sub>	-55 to +125	°C
Storage Temperature Range	T <sub>stg</sub>	-55 to +150	°C

Characteristics at Ta = 25°C

Parameter	Symbol	Conditions	Minimum	Typical	Maximum	Units
Reverse stand-off voltage	V <sub>RWM</sub>				7.0	V
Breakdown Voltage	V <sub>BR</sub>	I <sub>T</sub> =1mA	7.2			V
Reverse Leakage Current	I <sub>R</sub>	V <sub>RWM</sub> =7V,Ta=25°C			0.1	uA
Clamping Voltage	V <sub>C</sub>	I <sub>PP</sub> =1A, tp=8/20us I <sub>PP</sub> =6A, tp=8/20us I <sub>PP</sub> =16A, tp=100ns		12	10 13	V
Junction Capacitance	C <sub>j</sub>	V <sub>R</sub> =0V,f=1MHz V <sub>R</sub> =7V,f=1MHz			13 11	pF

Notes :

TLP parameter: Z<sub>0</sub> = 50Ω, tp = 100ns, tr = 2ns, averaging window from 60ns to 80ns.  
RDYN is calculated from 4A to 16A.

Fig.1 Pulse Waveform

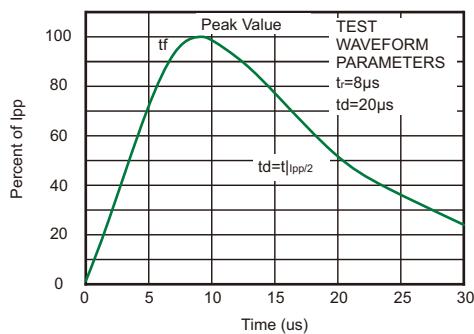
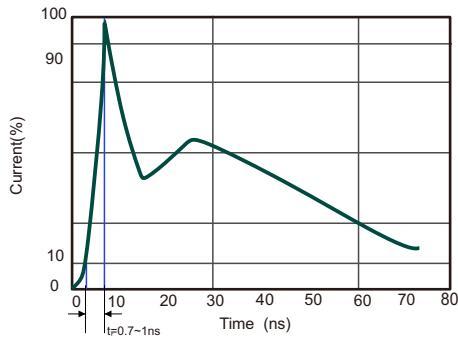
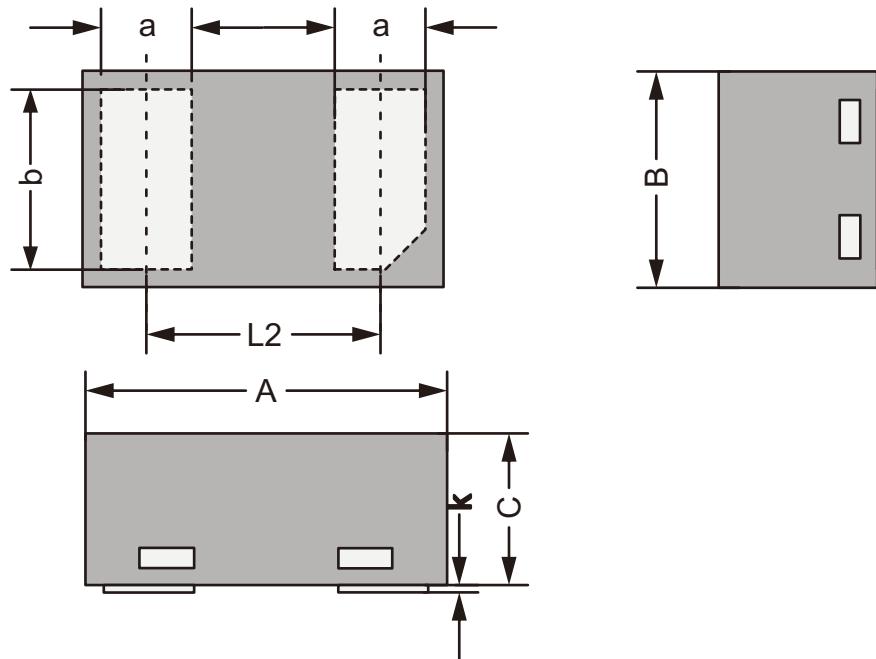


Fig.2 Contact discharge current waveform per IEC61000-4-2





### DFN1006-2L Package Outline Dimensions



DFN1006-2L mechanical data

UNIT		A	B	C	L2	a	b	k
mm	max	1.05	0.65	0.55	0.65 REF	0.29	0.54	0.03
	min	0.95	0.55	0.45		0.21	0.46	0.00
mil	max	41.34	25.59	21.65	25.59 REF	11.42	21.26	55.12
	min	37.40	21.65	17.72		8.27	18.11	1.18

### Marking

Type number	Marking code
ESDB7V0DS2A	7A



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